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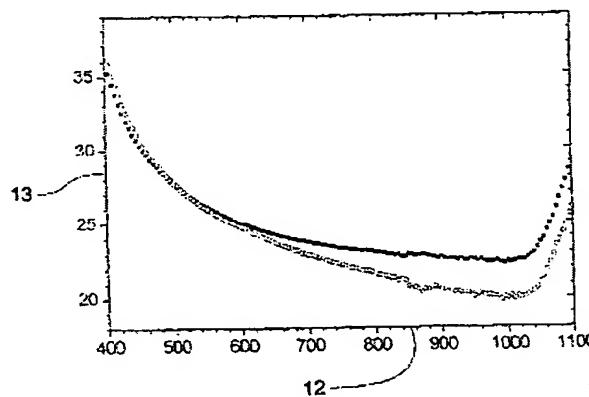
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(54) Title: METHOD FOR TEXTURING SURFACES OF SILICON WAFERS



(57) **Abstract:** In a method for texturing surfaces of silicon wafers comprising the steps of dipping the silicon wafers in an etching solution of water, concentrated hydrofluoric acid and concentrated nitric acid and setting a temperature for the etching solution, it is provided that the etching solution comprises, in percent, 20% to 55% water, 10% to 40% concentrated hydrofluoric acid and 20% to 60% concentrated nitric acid and that the temperature of the etching solution is between 0 and 15 degrees Celsius. This results in a comparatively higher efficiency due to reduced reflection by the silicon wafers.



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